

INTEGRATED STRUCTURE OF INDUCTANCES WITH SHARED VALUES ON A  
SEMICONDUCTOR SUBSTRATE

ABSTRACT OF THE DISCLOSURE

An integrated circuit including a structure of inductances on a semiconductor substrate, intended for operating at frequencies greater than several hundreds of MHz, including a first inductance formed by a conductive track and having first and second terminals respectively connected to each of the two ends of the conductive track, including a second inductance formed by the conductive track between the second terminal and any intermediary point of the conductive track connected to a third terminal, said second and third terminals forming the two terminals of the second inductance, and means for setting the third terminal to high impedance when the first inductance is used.

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